Silicon Epitaxial Planar Diodes

High Voltage Switching Diode

For high voltage and high speed switching applications





SOT-323 Plastic Package
Marking Code: F5

Absolute Maximum Ratings $(T_a = 25 \, ^{\circ}C)$

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	250	V
Reverse Voltage	V _R	200	V
Average Rectified Forward Current	I _{F(AV)}	100	mA
Maximum Peak Forward Current	I _{FM}	300	mA
Non-repetitive Peak Forward Surge Current (tp = 10 ms)	I _{FSM}	2	А
Power Dissipation	P _D	200	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10$ mA at $I_F = 100$ mA	V _F V _F	1 1.2	V
Reverse Current at $V_R = 50 \text{ V}$ at $V_R = 200 \text{ V}$	I _R	0.1 1	μΑ
Total Capacitance at V _R = 0, f = 1 MHz	Ст	3	pF
Reverse Recovery Time at I _F = 10 mA	t _{rr}	60	ns ns



(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



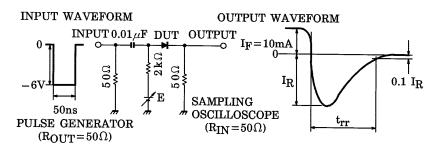


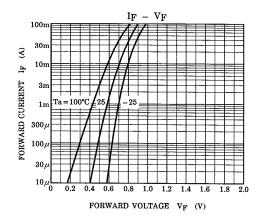


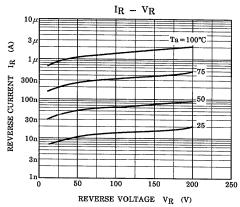


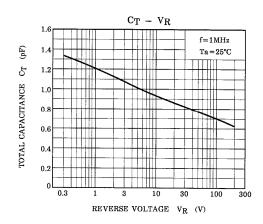


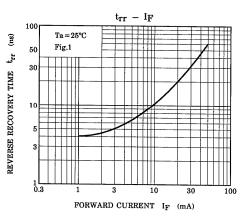
Reverse Recovery Time (trr) Test Circuit













SEMTECH ELECTRONICS LTD.









